

Silicon PNP Power Transistors

2SB600

DESCRIPTION

- With TO-3 package
- High power dissipations
- Complement to type 2SD555

APPLICATIONS

- For use in audio and power amplifier applications

PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Emitter |
| 3 | Collector |

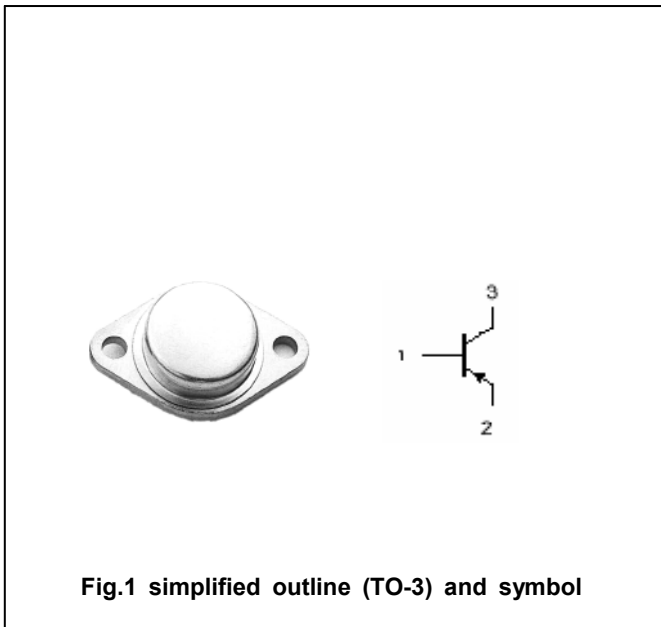


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|---------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -200 | V |
| V _{CEO} | Collector-emitter voltage | Open base | -200 | V |
| V _{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I _C | Collector current | | -10 | A |
| P _C | Collector power dissipation | T _C =25□ | 200 | W |
| T _j | Junction temperature | | 150 | □ |
| T _{stg} | Storage temperature | | -55~200 | □ |

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CHARACTERISTICS

Tj=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---------------|--------------------------------------|---------------------------|------|------|------|------|
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage | $I_C=-25mA ; I_B=0$ | -200 | | | V |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage | $I_E=-1mA ; I_C=0$ | -5 | | | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C=-10A ; I_B=-1A$ | | | -1.5 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C=-10A ; I_B=-1A$ | | | -2.0 | V |
| I_{CBO} | Collector cut-off current | $V_{CB}=-200V ; I_E=0$ | | | -0.1 | mA |
| I_{EBO} | Emitter cut-off current | $V_{EB}=-5V ; I_C=0$ | | | -0.1 | mA |
| h_{FE} | DC current gain | $I_C=-2A ; V_{CE}=-5V$ | 20 | | | |
| f_T | Transition frequency | $I_C=-0.5A ; V_{CE}=-10V$ | 4 | | | MHz |

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)